



# PIMC31PAS-Q

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor;  
R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

31 August 2023

Product data sheet

## 1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a medium power SOT1118D (DFN2020D-6) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks (SWF).

NPN/PNP complement: PIMN31PAS-Q

PNP/PNP complement: PIMP31PAS-Q

## 2. Features and benefits

- 500 mA output current capability
- Built-in resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Digital applications
- Cost-saving alternative to BC807 / BC817 series in digital applications
- Control of IC inputs
- Switching loads

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Per transistor</b>							
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	-	50	V
I <sub>O</sub>	output current		[1]	-	-	500	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[2]	0.7	1	1.3	k $\Omega$
R2/R1	bias resistor ratio		[2]	9	10	11	

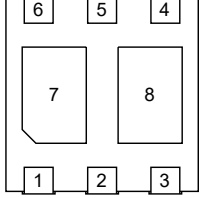
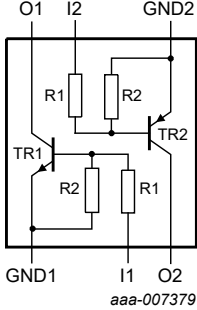
[1] For the PNP transistor with negative polarity.

[2] See section "Test information" for resistor calculation and test conditions.

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 1 kΩ, R2 = 10 kΩ

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	 <p>Transparent top view <b>DFN2020D-6 (SOT1118D)</b></p>	 <p>aaa-007379</p>
2	I1	input (base) TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	O1	output (collector) TR1		
7	O1	output (collector) TR1		
8	O2	output (collector) TR2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
<a href="#">PIMC31PAS-Q</a>	DFN2020D-6	plastic, leadless thermally enhanced ultra thin and small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	<a href="#">SOT1118D</a>

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PIMC31PAS-Q	8E

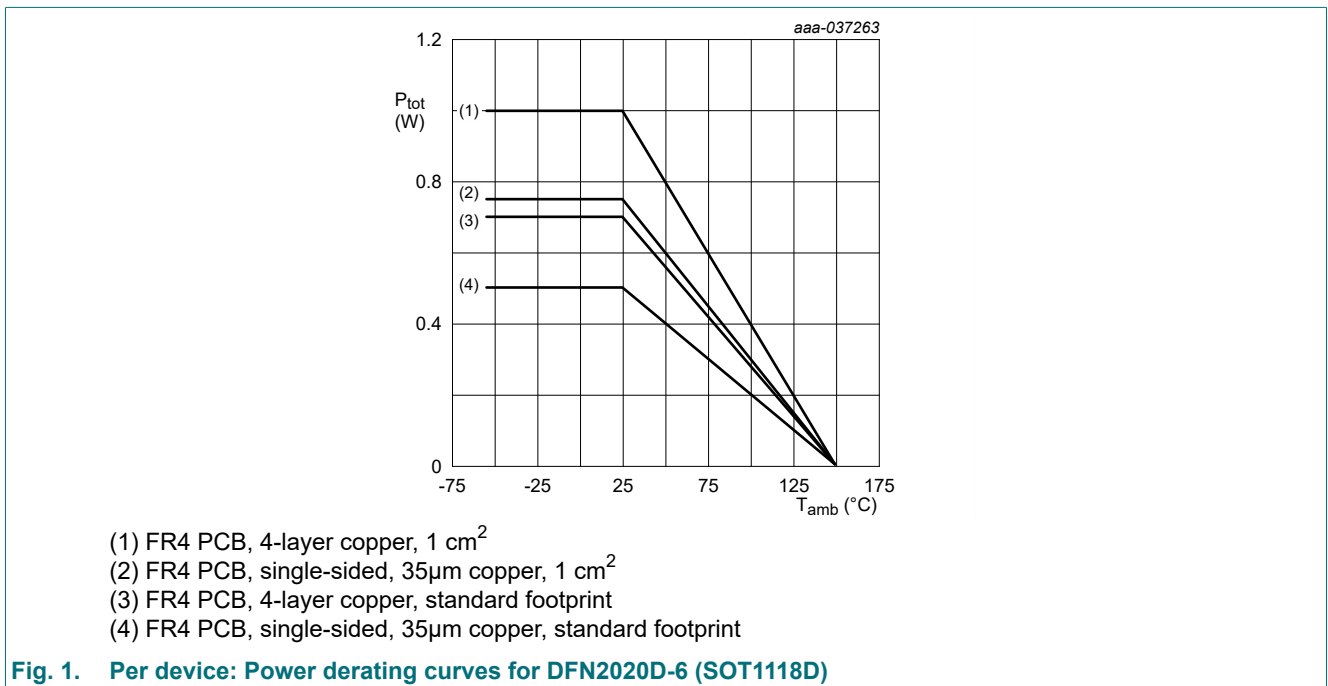
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
<b>Per transistor</b>						
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	[1]	-	5	V
V <sub>I</sub>	input voltage		[1]	-5	10	V
I <sub>O</sub>	output current		[1]	-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	360	mW
			[3]	-	550	mW
			[4]	-	510	mW
			[5]	-	730	mW
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	500	mW
			[3]	-	750	mW
			[4]	-	700	mW
			[5]	-	1	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 μm copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided, 35μm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

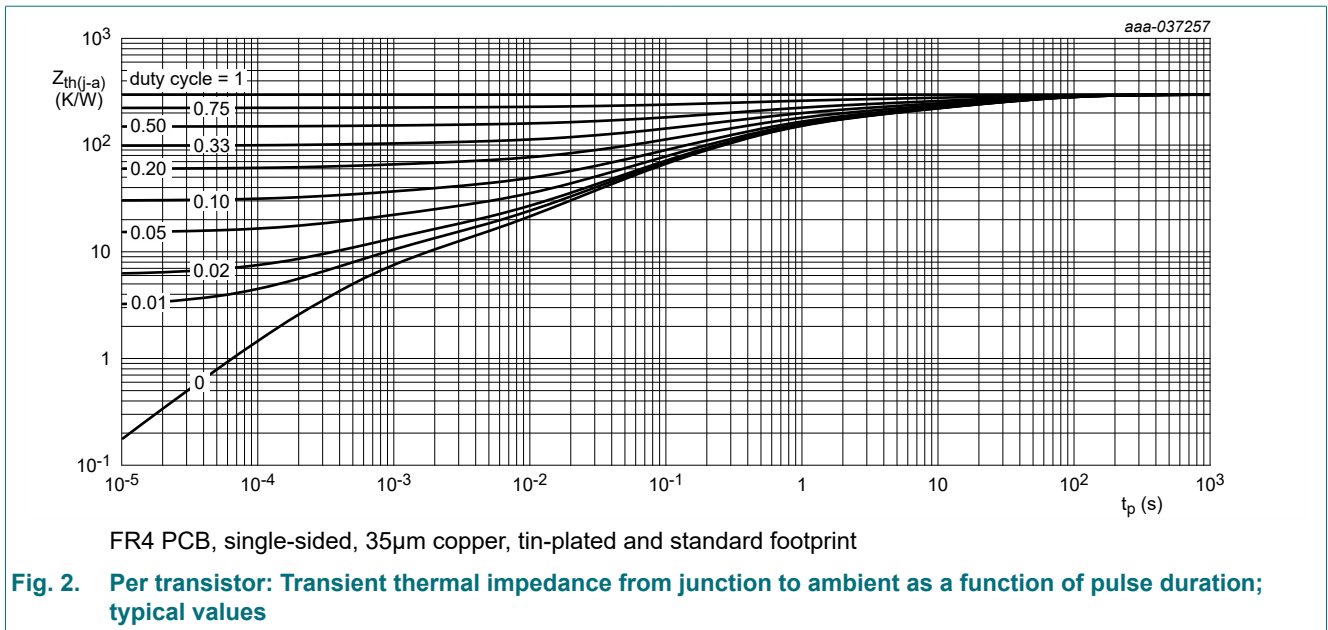


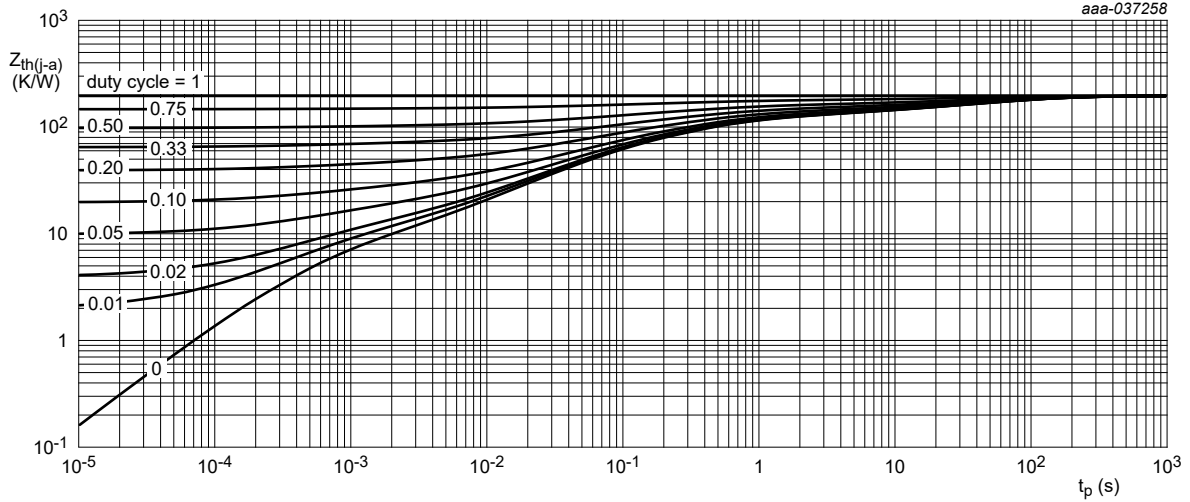
### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Per transistor</b>							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	348	K/W
			[2]	-	-	228	K/W
			[3]	-	-	246	K/W
			[4]	-	-	172	K/W
<b>Per device</b>							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	167	K/W
			[3]	-	-	179	K/W
			[4]	-	-	125	K/W

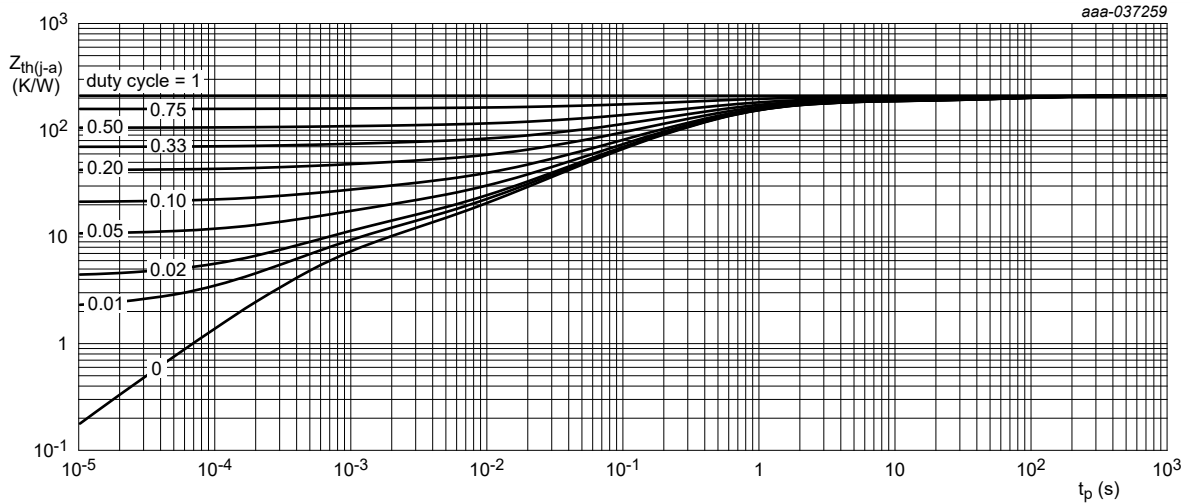
- [1] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.





FR4 PCB, single-sided, 35μm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

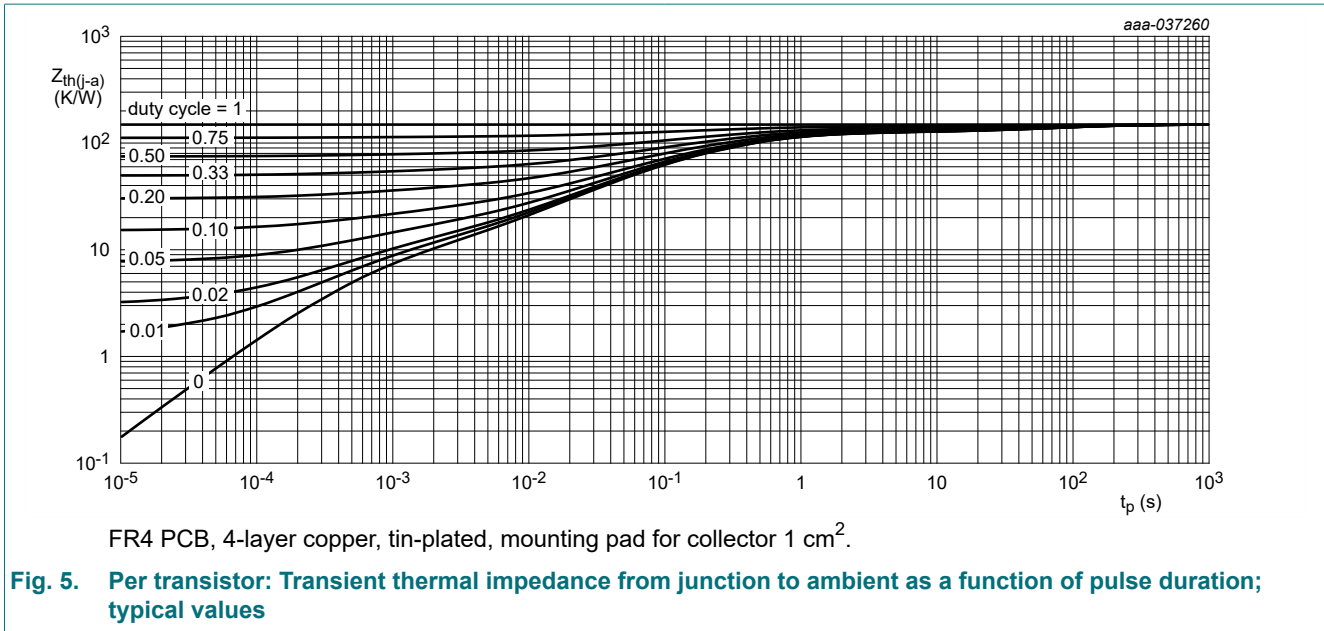
**Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

**Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 1 kΩ, R2 = 10 kΩ



## 10. Characteristics

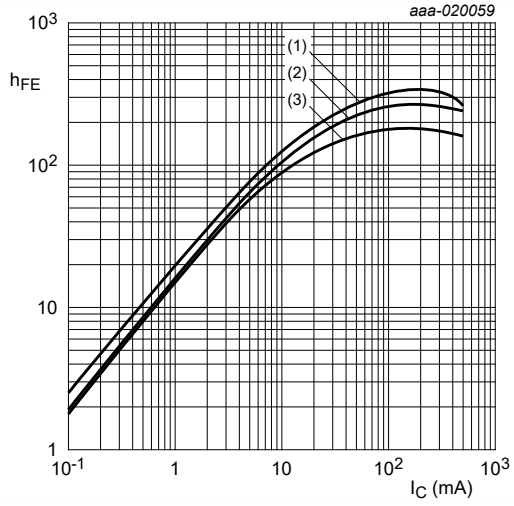
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Per transistor</b>							
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \mu\text{A}$ ; $I_E = 0 \text{ A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}$ ; $I_B = 0 \text{ A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50 \text{ V}$ ; $I_E = 0 \text{ A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}$ ; $I_B = 0 \text{ A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	0.5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5 \text{ V}$ ; $I_C = 0 \text{ A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	0.72	mA
$h_{FE}$	DC current gain	$V_{CE} = 5 \text{ V}$ ; $I_C = 50 \text{ mA}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	70	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 50 \text{ mA}$ ; $I_B = 2.5 \text{ mA}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}$ ; $I_C = 100 \mu\text{A}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	0.3	0.6	1	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}$ ; $I_C = 20 \text{ mA}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	0.4	0.8	1.4	V
R1	bias resistor 1 (input)	$T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[2]	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		[2]	9	10	11	
<b>TR1 (NPN)</b>							
$C_c$	collector capacitance	$V_{CB} = 10 \text{ V}$ ; $I_E = 0 \text{ A}$ ; $i_e = 0 \text{ A}$ ; $f = 1 \text{ MHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	5	-	pF
$f_T$	transition frequency	$V_{CE} = 5 \text{ V}$ ; $I_C = 50 \text{ mA}$ ; $f = 100 \text{ MHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	210	-	MHz
<b>TR2 (PNP)</b>							
$C_c$	collector capacitance	$V_{CB} = -10 \text{ V}$ ; $I_E = 0 \text{ A}$ ; $i_e = 0 \text{ A}$ ; $f = 1 \text{ MHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	7	-	pF
$f_T$	transition frequency	$V_{CE} = -5 \text{ V}$ ; $I_C = -50 \text{ mA}$ ; $f = 100 \text{ MHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	150	-	MHz

[1] For the PNP transistor with negative polarity.

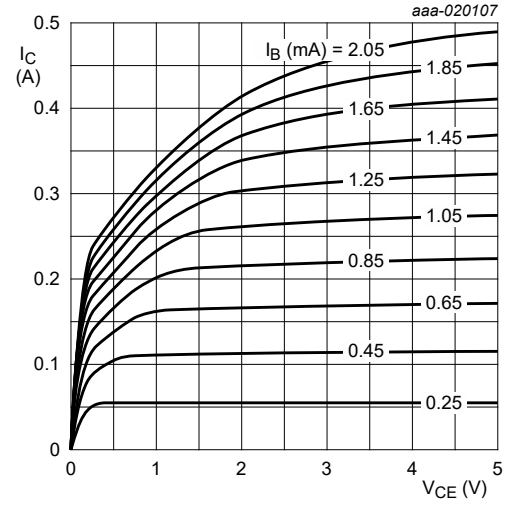
[2] See section "Test information" for resistor calculation and test conditions.

[3] Characteristics of built-in transistor.



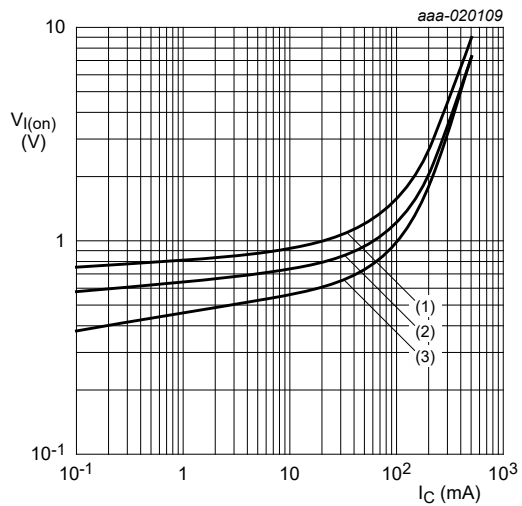
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig. 6. TR1 (NPN): DC current gain as a function of collector current; typical values**



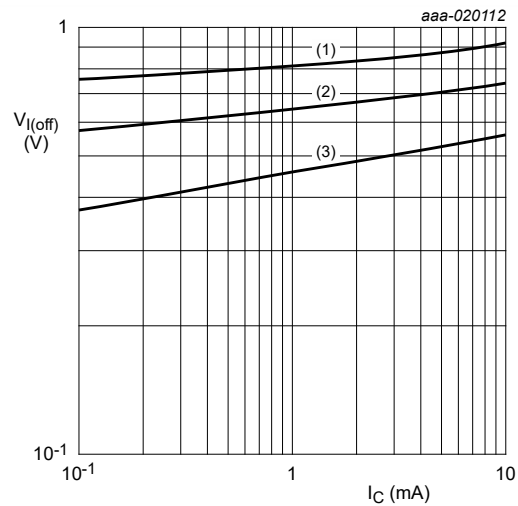
$T_{amb} = 25\text{ °C}$

**Fig. 7. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values**



$V_{CE} = 0.3\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

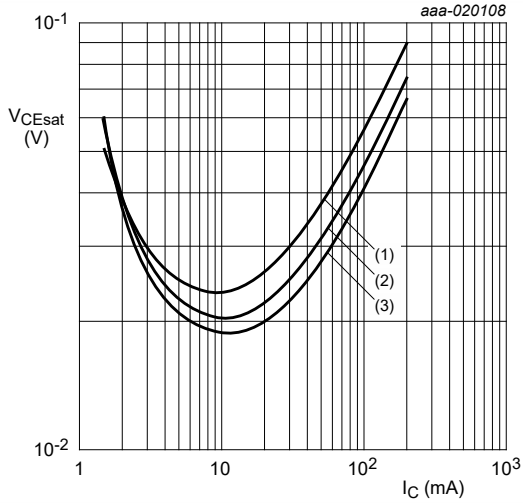
**Fig. 8. TR1 (NPN): On-state input voltage as a function of collector current; typical values**



$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

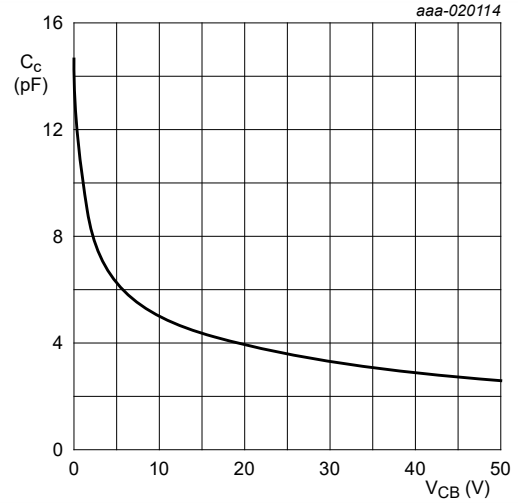
**Fig. 9. TR1 (NPN): Off-state input voltage as a function of collector current; typical values**





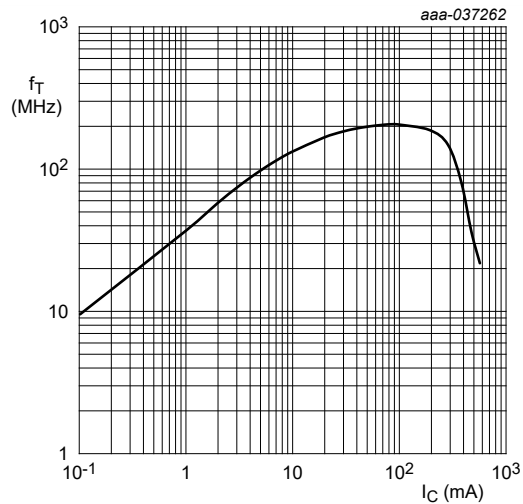
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 10. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



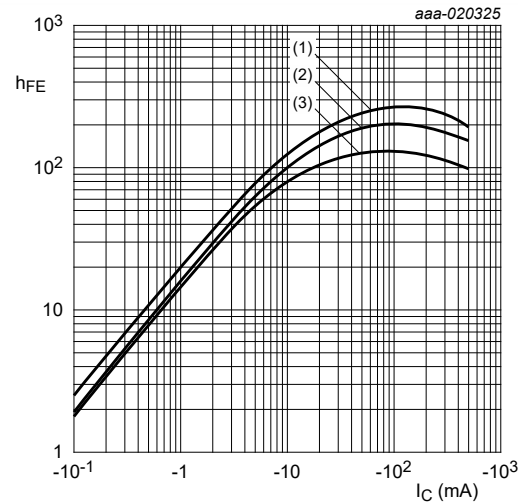
$f = 1\text{ MHz}$   
 $T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 11. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



$f = 100\text{ MHz}$ ;  $V_{CE} = -5\text{ V}$   $T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 12. TR2 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 13. TR2 (PNP): DC current gain as a function of collector current; typical values

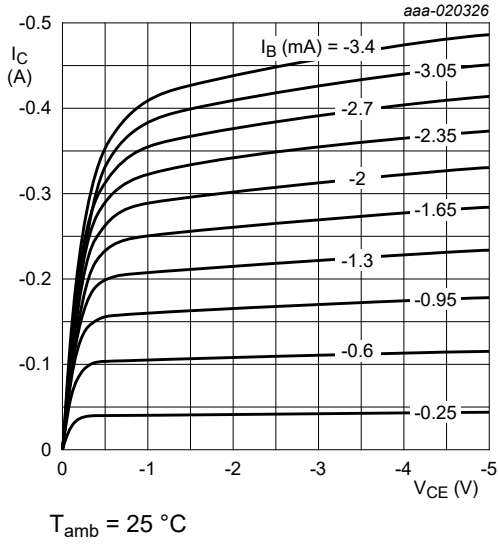


Fig. 14. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values

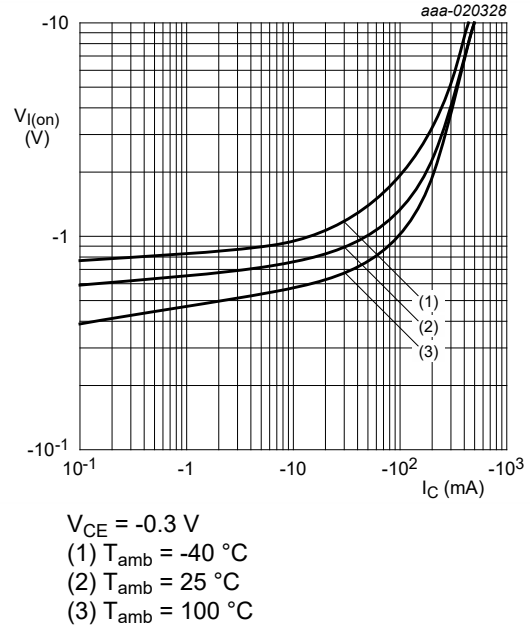


Fig. 15. TR2 (PNP): On-state input voltage as a function of collector current; typical values

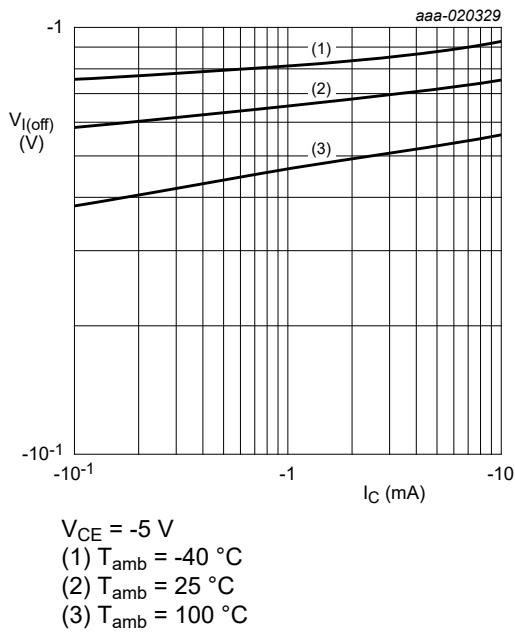


Fig. 16. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

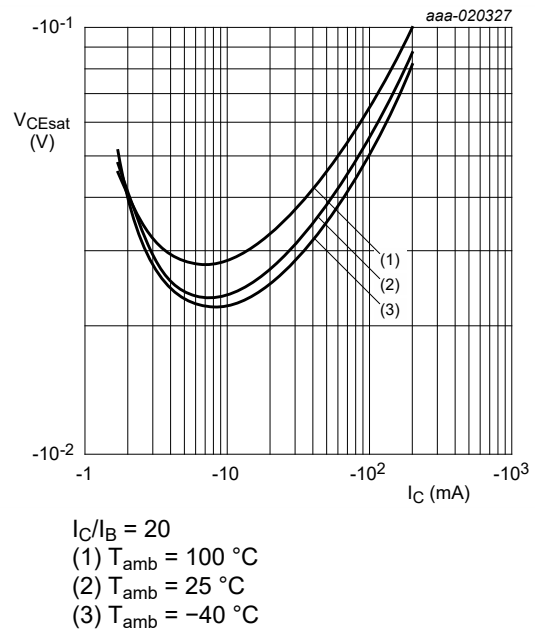
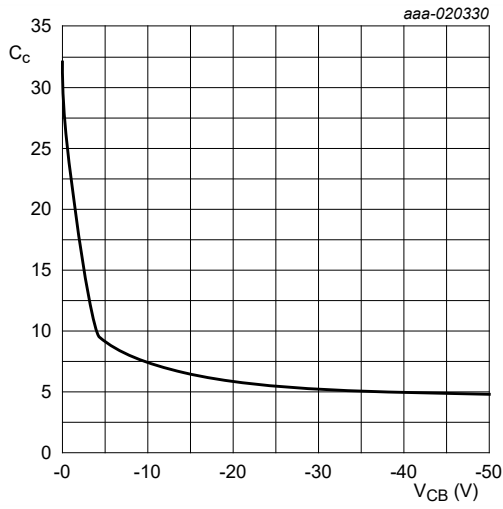
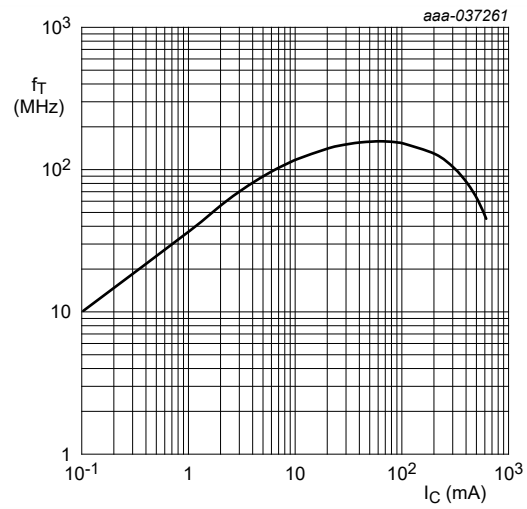


Fig. 17. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$f = 1 \text{ MHz}$   
 $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 18. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



$f = 100 \text{ MHz}; V_{CE} = 5 \text{ V } T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 19. TR1 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

## 11. Test information

### Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### Resistor calculation

- Calculation of bias resistor 1 (R1):

$$R_1 = \frac{V(I_2) - V(I_1)}{I_2 - I_1}$$

- Calculation of bias resistor ratio (R2/R1):

$$\frac{R_2}{R_1} = \frac{V(I_4) - V(I_3)}{R_1 \cdot (I_4 - I_3)} - 1$$

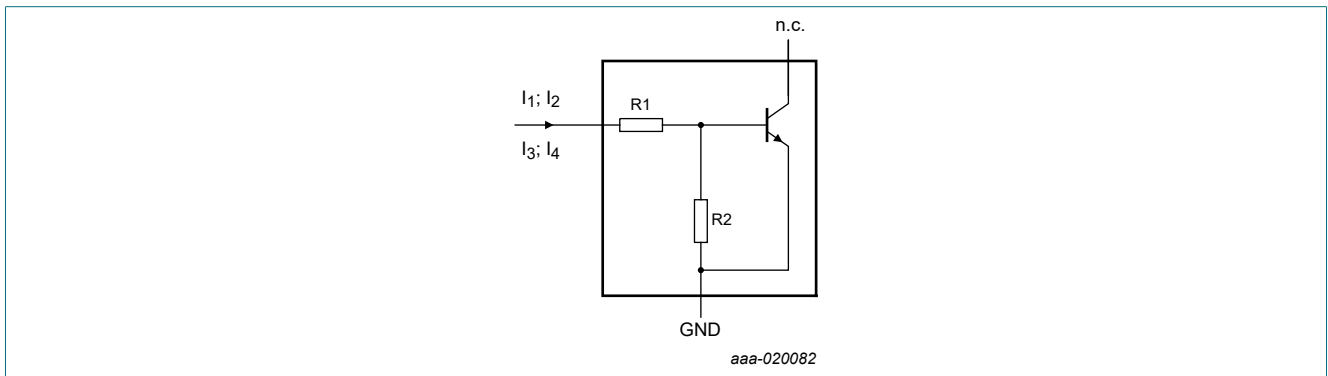


Fig. 20. NPN transistor: Resistor test circuit

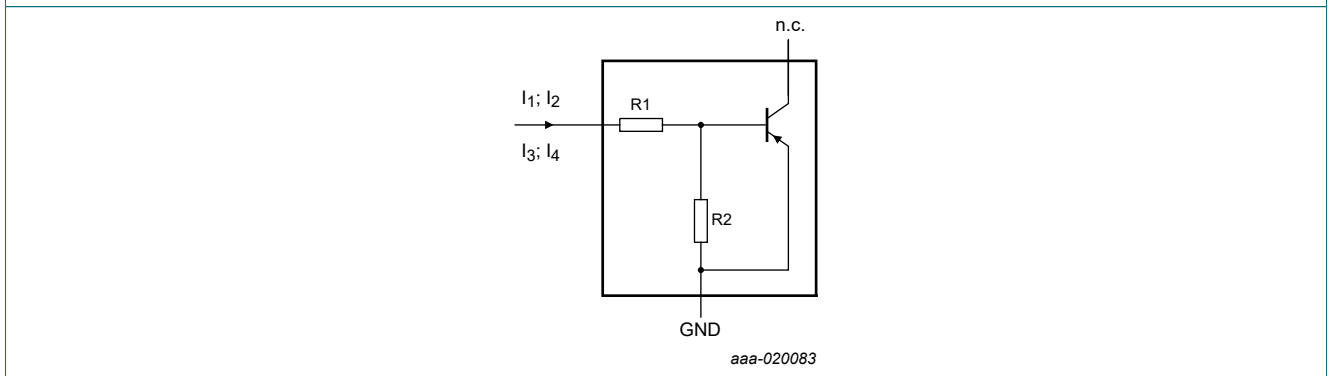


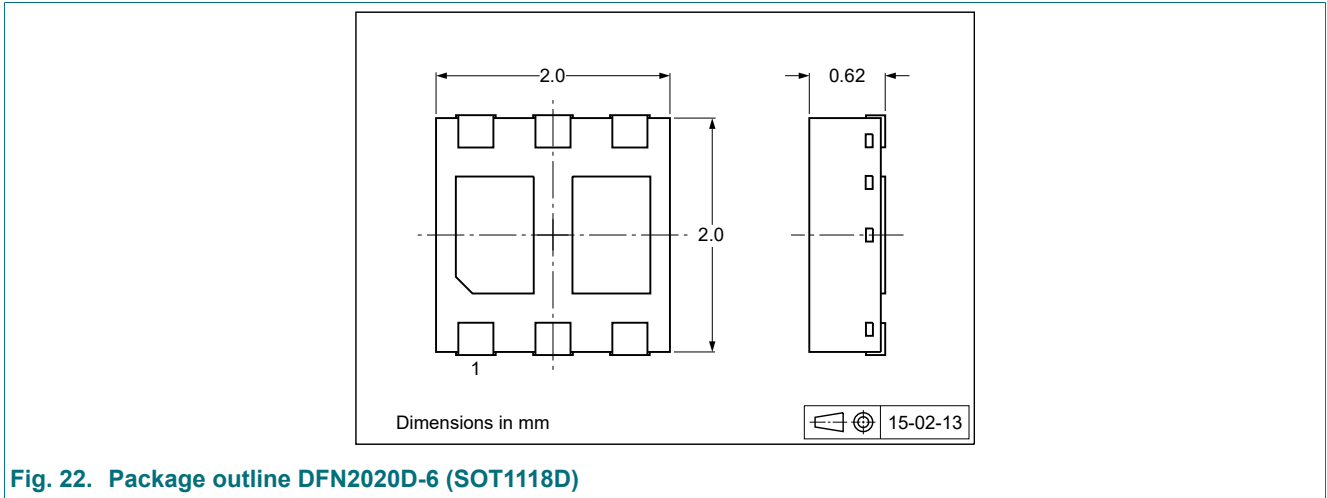
Fig. 21. PNP transistor: Resistor test circuit

### Resistor test conditions

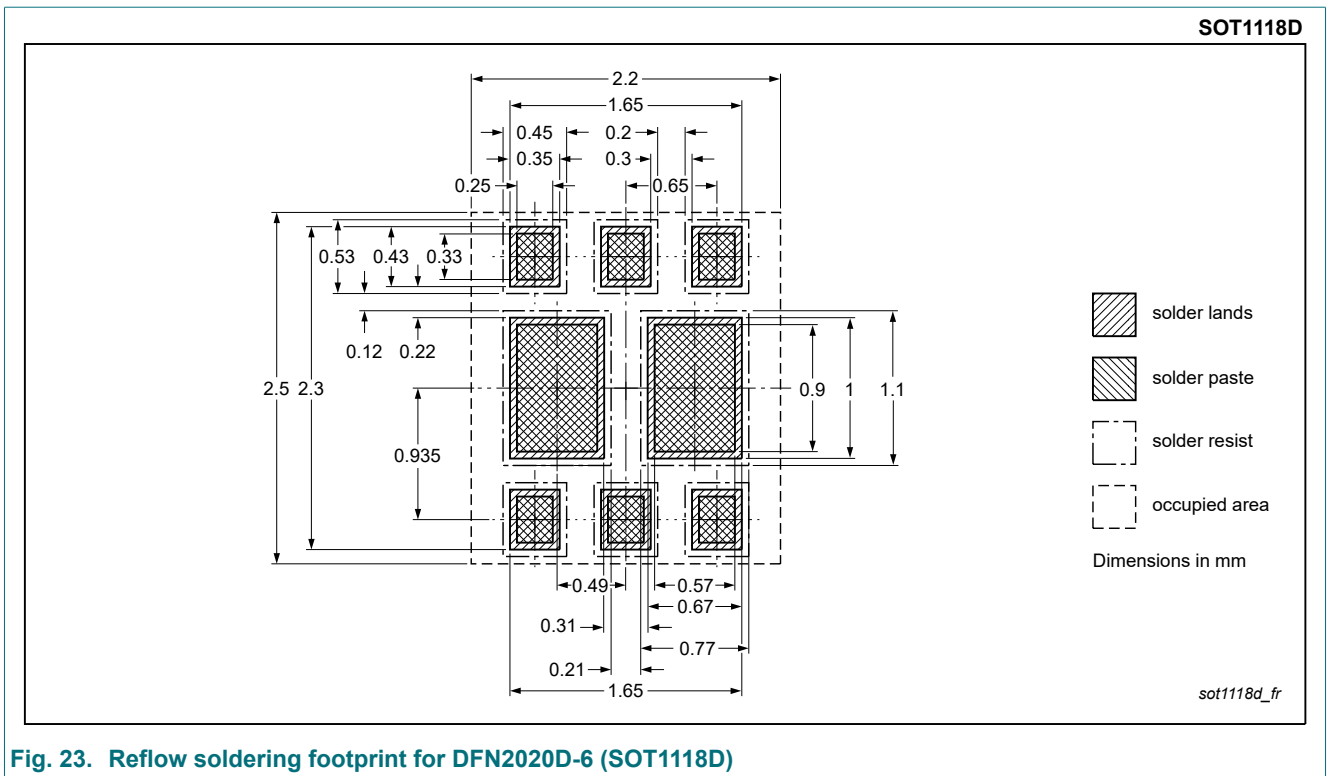
Table 8. Resistor test conditions

PIMC31PAS-Q	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I <sub>1</sub>	I <sub>2</sub>	I <sub>3</sub>	I <sub>4</sub>
TR1 (NPN)	1	10	0.7 mA	0.8 mA	-0.45 mA	-0.55 mA
TR2 (PNP)			-0.7 mA	-0.8 mA	0.45 mA	0.55 mA

## 12. Package outline



## 13. Soldering



## 14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMC31PAS-Q v.1	20230831	Product data sheet	-	-

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## Contents

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1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values.....	3
9. Thermal characteristics.....	4
10. Characteristics.....	7
11. Test information.....	12
12. Package outline.....	13
13. Soldering.....	13
14. Revision history.....	14
15. Legal information.....	15

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